L Number	Hits	Search Text	DB	Time stamp
1	2732731	memory or storage	USPAT;	2004/03/01 14:41
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT	
2	1974	(memory or storage) and cell with float\$5 not gate	USPAT;	2004/03/01 14:42
1			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
3	130	((memory or storage) and cell with float\$5 not gate) and cell with	USPAT;	2004/03/01 14:47
		transistor	US-PGPUB;	
			EPO; JPO;	
1.			DERWENT	
4	32	(((memory or storage) and cell with float\$5 not gate) and cell with	USPAT;	2004/03/01 14:43
		transistor) and pulse	US-PGPUB;	*
			EPO; JPO;	
			DERWENT	
5	98	(((memory or storage) and cell with float\$5 not gate) and cell with	USPAT;	2004/03/01 14:47
		transistor) not ((((memory or storage) and cell with float\$5 not gate) and	US-PGPUB;	
		cell with transistor) and pulse)	ЕРО; ЈРО;	
			DERWENT	

L Number	Hits	Search Text	DB	Time stamp
1	2732731	memory or storage	USPAT;	2004/03/01 15:03
			US-PGPUB;	
	•		EPO; JPO;	
2	1974	(memory or storage) and cell with float\$5 not gate	DERWENT USPAT;	2004/03/01 15:20
•	17/4	(monor) of storage) and cent with months not gate	US-PGPUB;	2004/03/01 13.20
			ЕРО; ЛРО;	
			DERWENT	
3	130	((memory or storage) and cell with float\$5 not gate) and cell with	USPAT;	2004/03/01 14:47
		transistor	US-PGPUB; EPO; JPO;	
			DERWENT	
4	32	(((memory or storage) and cell with float\$5 not gate) and cell with	USPAT;	2004/03/01 14:43
		transistor) and pulse	US-PGPUB;	
			ЕРО; ЈРО;	
-	^^	///	DERWENT	2004/02/01 14 15
5	98	(((memory or storage) and cell with float\$5 not gate) and cell with transistor) not ((((memory or storage) and cell with float\$5 not gate) and	USPAT; US-PGPUB;	2004/03/01 14:47
		cell with transistor) and pulse)	EPO; JPO;	
		The state of the party	DERWENT	
6	274	((memory or storage) and cell with float\$5 not gate) and (static or sram)	USPAT;	2004/03/01 14:53
			US-PGPUB;	
			EPO; JPO;	
7	8	(((memory or storage) and cell with float\$5 not gate) and (static or	DERWENT USPAT;	2004/03/01 14:54
'	0	sram)) and 365/\$.ccls.	US-PGPUB;	2004/03/01 14.54
		<i>"</i>	ЕРО; ЈРО;	
'			DERWENT	
8	54	((memory or storage) and cell with float\$5 not gate) and 365/\$.ccls.	USPAT;	2004/03/01 14:54
			US-PGPUB;	
			EPO; JPO; DERWENT	
9	805	(memory or storage) and cell with transistor with open	USPAT;	2004/03/01 15:08
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	
			ЕРО; ЛРО;	
10	430	((manage of stances) and call with transists with warm at 2000	DERWENT	2004/02/01 15 12
10	430	((memory or storage) and cell with transistor with open) and 365/\$.ccls.	USPAT; US-PGPUB;	2004/03/01 15:13
			EPO; JPO;	
			DERWENT	
11	36	((memory or storage) and cell with transistor with open) and	USPAT;	2004/03/01 15:13
		365/154.ccls.	US-PGPUB;	
			EPO; JPO; DERWENT	
12	7681	(memory or storage) and cell with (source or drain) with float\$5	USPAT;	2004/03/01 15:31
	7501	(US-PGPUB;	, 200 , 05/01 15.51
			ЕРО; ЛРО;	
			DERWENT	
13	3944	((memory or storage) and cell with (source or drain) with float\$5) and	USPAT;	2004/03/01 15:25
		365/\$.ccls.	US-PGPUB; EPO; JPO;	
			DERWENT	
14	41	((memory or storage) and cell with (source or drain) with float\$5) and	USPAT;	2004/03/01 15:25
]		365/154.ccls.	US-PGPUB;	
			ЕРО; ЛРО;	
15	2100	(mamory or storage) and cell with transistor with (source or drain) with	DERWENT	2004/02/01 15:51
12	3198	(memory or storage) and cell with transistor with (source or drain) with float\$5	USPAT; US-PGPUB;	2004/03/01 15:51
			ЕРО; ЛРО;	
			DERWENT	
			···	

16	94	((memory or storage) and cell with transistor with (source or drain) with	USPAT;	2004/03/01 15:33
		float\$5) and source with electrically adj floating	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT	
17	30	(((memory or storage) and cell with transistor with (source or drain)	USPAT;	2004/03/01 15:52
		with float\$5) and source with electrically adj floating) and pulse	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT	
18	465	((memory or storage) and cell with transistor with (source or drain) with	USPAT;	2004/03/01 15:53
		float\$5) and pulse with gate	US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT	